

ABSTRACT OF THE DISCLOSURE

Within a dual damascene method for forming a contiguous patterned conductor interconnect and patterned conductor stud layer within a corresponding trench contiguous with a corresponding via formed through a dielectric layer formed of a comparatively low dielectric constant dielectric material, the dielectric layer is, prior to dual damascene etching, formed of a patterned first dielectric layer having formed thereupon a blanket second dielectric layer. The patterned first dielectric layer is formed of a first dielectric material and the blanket second dielectric layer is formed of a second dielectric material, where each of the first dielectric material and the second dielectric material has a dielectric constant of less than about 4.0, but wherein the first dielectric material serves as an intrinsic etch stop when dual damascene etching the dielectric layer.